

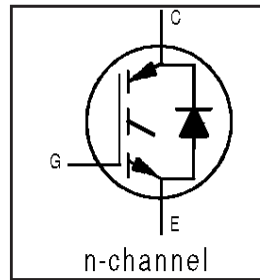
IRG4PH40KDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

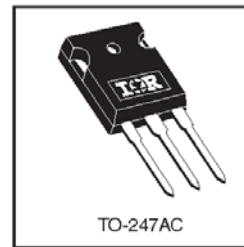
- High short circuit rating optimized for motor control, $t_{sc} = 10\mu s$, $V_{CC} = 720V$, $T_J = 125^\circ C$, $V_{GE} = 15V$
- Combines low conduction losses with high switching speed
- Tighter parameter distribution and higher efficiency than previous generations
- IGBT co-packaged with HEXFRED™ ultrafast, ultrasoft recovery antiparallel diodes
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 2.74V$
@ $V_{GE} = 15V, I_C = 15A$

Benefits

- Latest generation 4 IGBT's offer highest power density motor controls possible
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise, EMI and switching losses
- This part replaces the IRGPH40KD2 and IRGPH40MD2 products
- For hints see design tip 97003



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	30	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	15	
I_{CM}	Pulsed Collector Current ①	60	
I_{LM}	Clamped Inductive Load Current ②	60	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	8.0	
I_{FM}	Diode Maximum Forward Current	130	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_{STG}			
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	---	---	0.77	$^\circ C/W$
$R_{\theta JC}$	Junction-to-Case - Diode	---	---	1.7	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	---	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	---	40	
Wt	Weight	---	6 (0.21)	---	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.37	—	$V/^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.74	3.4	V	$I_C = 15A$ $I_C = 30A$ $I_C = 15A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig. 2, 5
		—	3.29	—		
		—	2.53	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-3.3	—	$mV/^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ^④	8.0	12	—	S	$V_{CE} = 100V, I_C = 15A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$ $V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
		—	—	3000		
V_{FM}	Diode Forward Voltage Drop	—	2.6	3.3	V	$I_C = 8.0A$ $I_C = 8.0A, T_J = 125^\circ\text{C}$ See Fig. 13
		—	2.4	3.1		
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (tum-on)	—	94	140	nC	$I_C = 15A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
Q_{ge}	Gate - Emitter Charge (tum-on)	—	14	22		
Q_{gc}	Gate - Collector Charge (tum-on)	—	37	55		
$t_{d(on)}$	Turn-On Delay Time	—	50	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 15A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail" and diode reverse recovery See Fig. 9,10,18
t_r	Rise Time	—	31	—		
$t_{d(off)}$	Turn-Off Delay Time	—	96	140		
t_f	Fall Time	—	220	330		
E_{on}	Turn-On Switching Loss	—	1.31	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,18
E_{off}	Turn-Off Switching Loss	—	1.12	—		
E_{ts}	Total Switching Loss	—	2.43	2.8		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	49	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11,18 $I_C = 15A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail" and diode reverse recovery
t_r	Rise Time	—	33	—		
$t_{d(off)}$	Turn-Off Delay Time	—	290	—		
t_f	Fall Time	—	440	—		
E_{ts}	Total Switching Loss	—	5.1	—	mJ	Measured 5mm from package
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	1600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
C_{oes}	Output Capacitance	—	77	—		
C_{res}	Reverse Transfer Capacitance	—	26	—		
t_{rr}	Diode Reverse Recovery Time	—	63	95	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$ 14
		—	106	160		
I_{rr}	Diode Peak Reverse Recovery Current	—	4.5	8.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$ 15
		—	6.2	11		
Q_{rr}	Diode Reverse Recovery Charge	—	140	380	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$ 16
		—	335	880		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	133	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$ 17
		—	85	—		

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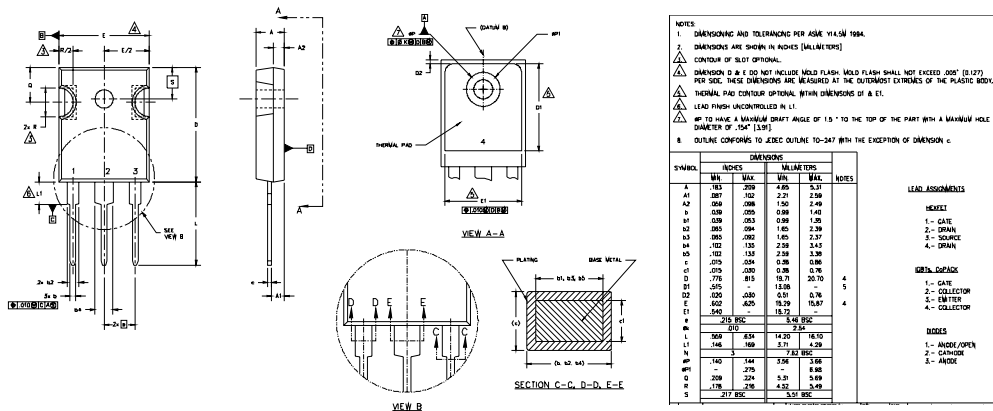
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Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=10\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.

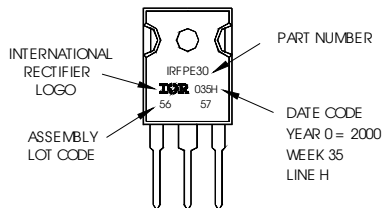
TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFP30
WITH ASSEMBLY
LOT CODE 5667
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"
Note: "P" in assembly line
position indicates "Lead-Free"



Data and specifications subject to change without notice.

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